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Nota di bibliografia	Includes bibliographical references and index.
Nota di contenuto	Introduction -- Design of Double-Pole Four-Throw RF Switch -- Design of Double-Gate MOSFET -- Double-Pole Four-Throw RF Switch Based on Double-Gate MOSFET -- Cylindrical Surrounding Double-Gate RF MOSFET -- Hafnium Dioxide Based Double-Pole Four-Throw Double-Gate RF CMOS Switch -- Testing of MOSFET Surfaces Using Image Acquisition -- Conclusions and Future Scope.
Sommario/riassunto	This book provides analysis and discusses the design of various MOSFET technologies which are used for the design of Double-Pole Four-Throw (DP4T) RF switches for next generation communication systems. The authors discuss the design of the (DP4T) RF switch by using the Double-Gate (DG) MOSFET, as well as the Cylindrical Surrounding double-gate (CSDG) MOSFET. The effect of HFO2 (high dielectric material) in the design of DG MOSFET and CSDG MOSFET is also explored. Coverage includes comparison of Single-gate MOSFET and Double-gate MOSFET switching parameters, as well as testing of MOSFETs parameters using image acquisition. · Provides a single-source reference to the latest technologies for the design of Double-

gate MOSFET, Cylindrical Surrounding double-gate MOSFET and HFO2 based MOSFET; · Explains the design of RF switches using the technologies presented and simulates switches; · Verifies parameters and discusses feasibility of devices and switches.